

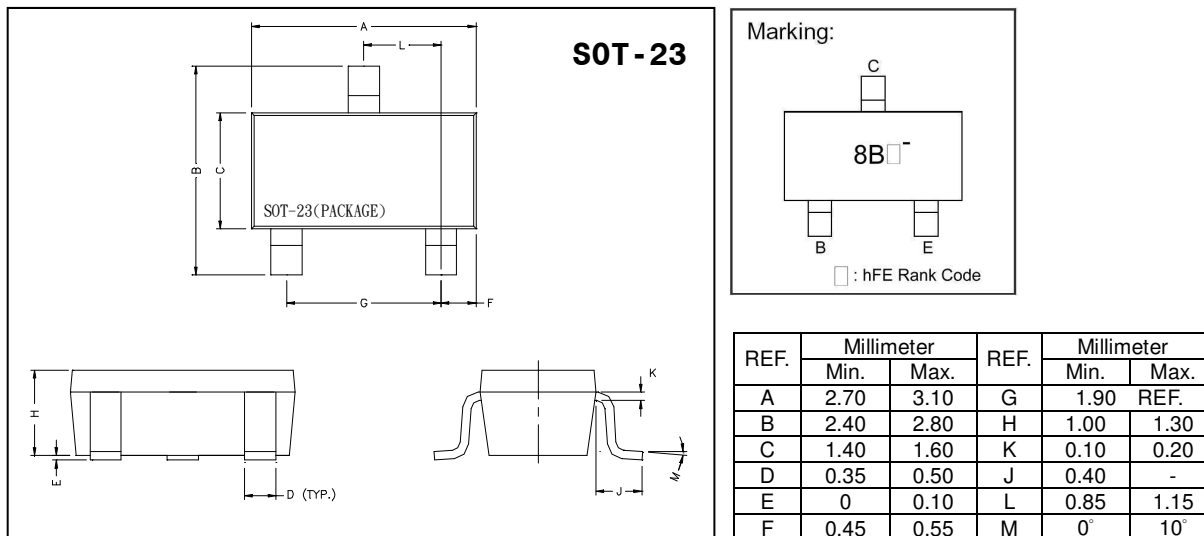
GBC847

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GBC847 is designed for switching and AF amplifier application, suitable for automatic insertion in thick and thin-film circuits.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	VCBO	50	V
Collector to Emitter Voltage	VCEO	45	V
Emitter to Base Voltage	VEBO	6	V
Collector Current	I _C	100	mA
Total Power Dissipation	PD	225	mW

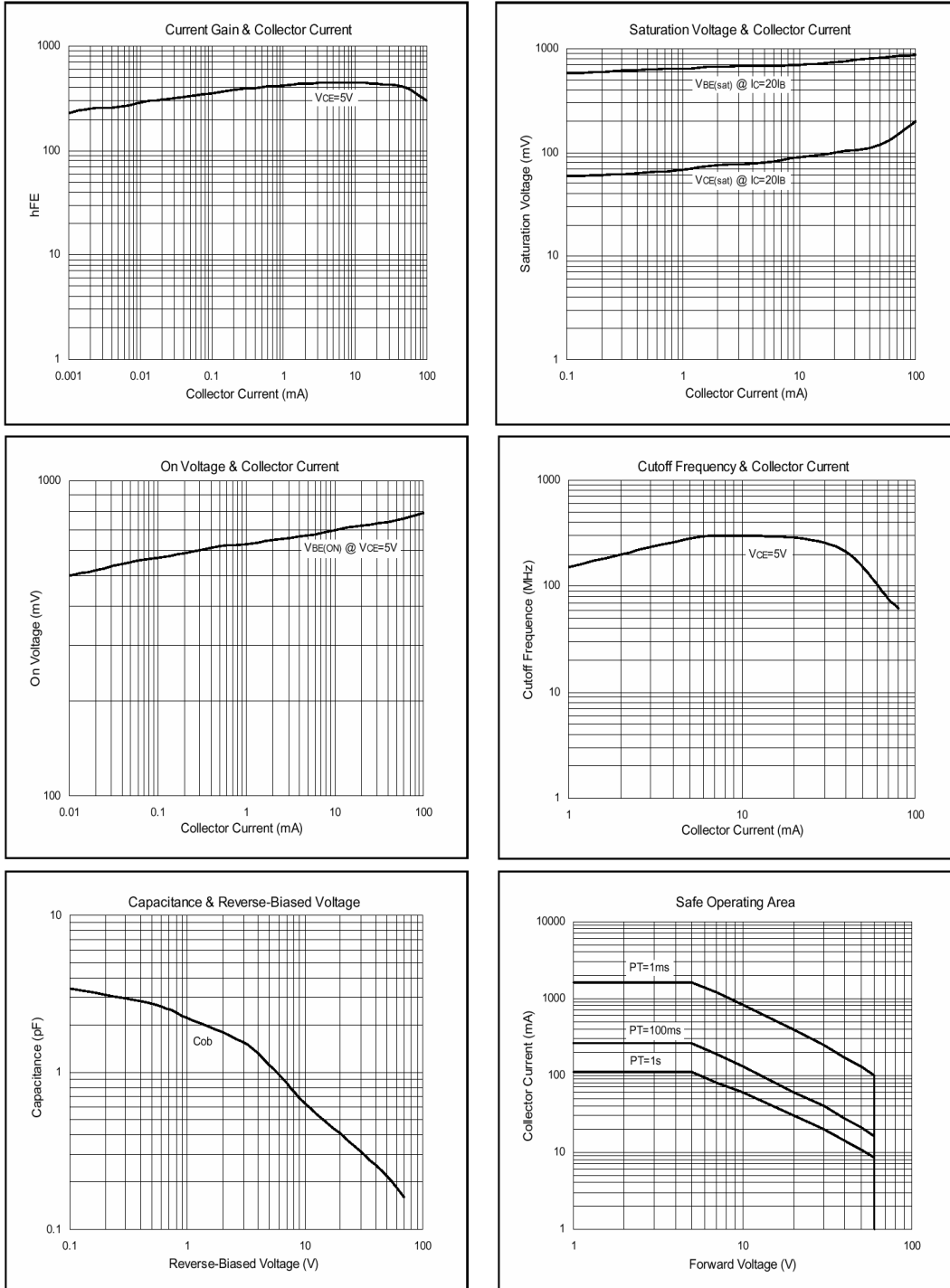
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	50	-	-	V	I _C =100μA
BVCEO	45	-	-	V	I _C =1mA
BVEBO	6	-	-	V	I _E =10μA
ICBO	-	-	15	nA	V _{CB} =30V
VCE(sat)1	-	90	250	mV	I _C =10mA, I _B =0.5mA
VCE(sat)2	-	200	600	mV	I _C =100mA, I _B =5mA
VBE(sat)1	-	700	-	mV	I _C =10mA, I _B =0.5mA
VBE(sat)2	-	900	-	mV	I _C =100mA, I _B =5mA
VBE(on)1	580	-	700	mV	V _{CE} =5V, I _C =2mA
VBE(on)2	-	-	770	mV	V _{CE} =5V, I _C =10mA
hFE	110	-	800		V _{CE} =5V, I _C =2mA
f _T	-	300	-	MHz	V _{CE} =5V, I _C =10mA
C _{ob}	-	3.5	6	pF	V _{CB} =10V, f=1MHz, I _E =0A

Classification Of hFE

Rank	A	B	C
hFE	110-220	200-450	450-800

Characteristics Curve



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